

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1050	372/108.CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/09/03 15:44
L2	177	372/45.012.CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/09/03 16:04
S1	4	("6333945") or ("20020041613") or ("20040089866") or ("6606334").PN.	US-PGPUB; USPAT	OR	OFF	2007/12/31 07:21
S2	1	substrate near3 inp and single near3 mode near3 fib\$3 and mqw and fundamental near3 lateral near3 mode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2007/12/31 08:30
S3	28	substrate near3 inp and single near3 mode near3 fib\$3 and mqw and fundamental near3 mode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2007/12/31 07:23
S4	52	substrate and inp and single near3 mode near3 fib\$3 and mqw and fundamental near3 mode\$1	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2007/12/31 08:31
S5	24	S4 not S3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2007/12/31 09:35
S6	160	semiconductor near3 laser and coupl\$3 with single near3 mode near3 fib\$3 and mqw	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2007/12/31 09:42
S7	81	S6 and "372"/\$.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2007/12/31 09:37

S8	6	semiconductor near3 laser and coupl\$3 with single near3 mode near3 fib\$3 and mqw with width	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2007/12/31 10:36
S9	9	semiconductor near3 laser and substrate near3 inp and clad\$4 near3 inp and mqw with width and fundamental near3 mode\$1	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2007/12/31 10:44
S10	9	semiconductor near3 laser and substrate near3 inp and clad\$4 near3 inp and mqw and fundamental near3 mode\$1 and sch	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2007/12/31 10:52
S11	202	semiconductor near3 laser and substrate near3 inp and clad\$4 near3 inp and mqw and sch and ingaasp	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2007/12/31 10:52
S12	202	semiconductor near3 laser and substrate near3 inp and clad\$4 near3 inp and mqw and sch and ingaasp and sch	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2007/12/31 11:04
S13	68	semiconductor near3 laser and substrate near3 inp and clad\$4 near3 inp and mqw and sch and clad\$4 near3 ingaasp and sch	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2007/12/31 11:05
S14	68	semiconductor near3 laser and substrate near3 inp and clad\$4 near3 inp and mqw and sch and clad\$4 near3 ingaasp	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2007/12/31 11:05
S15	7	ocl and "372"/\$.cols.	USPAT	OR	OFF	2008/01/02 09:21
S16	0	butt near3 coupl\$3 near3 fib\$3 same mqw with width and semiconductor near3 laser	USPAT	OR	OFF	2008/01/02 09:22
S17	0	butt\$3 near3 fib\$3 same mqw with width and semiconductor near3 laser	USPAT	OR	OFF	2008/01/02 09:23

S18	0	butt\$3 near3 fib\$3 same mqw and semiconductor near3 laser	USPAT	OR	OFF	2008/01/02 09:23
S19	13	butt\$3 near3 fib\$3 and mqw same semiconductor near3 laser	USPAT	OR	OFF	2008/01/02 09:25
S20	44	but\$3 with fib\$3 and mqw same semiconductor near3 laser	USPAT	OR	OFF	2008/01/02 09:27
S21	49	pigtail with semiconductor near3 laser	USPAT	OR	OFF	2008/01/02 09:28
S22	3	pigtail with semiconductor near3 laser and mqw	USPAT	OR	OFF	2008/01/02 09:28
S23	698	372/19.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/09/03 10:32
S24	448	372/109.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/09/03 10:46
S25	601	372/39.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/09/03 10:55
S26	1415	372/43.01.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/09/03 11:07
S27	179	372/54.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/09/03 11:40
S28	525	372/66.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/09/03 11:43

S29	538	372/103.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/09/03 11:54
S30	73	(yasuaki near3 nagashima).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/09/03 12:19
S31	20	S30 and semiconductor near3 laser	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/09/03 12:19
S32	3	S30 and semiconductor near3 laser and width and bandgap	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/09/03 12:20
S33	1078	(atsushi near3 yamada).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/09/03 12:21
S34	3	S33 and semiconductor near3 laser and width and bandgap	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/09/03 12:21
S35	17	(yoshiharu near3 shimose).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/09/03 12:37
S36	2	S35 and semiconductor near3 laser and width and bandgap	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/09/03 12:37
S37	20	(tomoyuki near3 kikugawa).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/09/03 12:38
S38	3	S37 and semiconductor near3 laser and width and bandgap	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/09/03 12:39

S39	434	semiconductor near3 laser and width and bandgap and single near3 mode near3 fib\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/09/03 12:47
S40	116	semiconductor near3 laser and width and bandgap and single near3 mode near3 fib\$3 and spot near3 size\$1	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/09/03 12:48
S41	207	semiconductor near3 laser and substrate near3 inp and clad\$4 near3 inp and mqw and sch and ingaasp	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/09/03 13:06
S42	0	(semiconductor near3 laser and width and bandgap and single near3 mode near3 fib\$3 and spot near3 size\$1). clm.	US-PGPUB	OR	ON	2008/09/03 13:12
S43	1	(semiconductor near3 laser and width and bandgap and single near3 mode near3 fib \$3).clm.	US-PGPUB	OR	ON	2008/09/03 13:12

9/3/08 4:09:15 PM

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